NTE ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE586
Silicon Rectifier Diode
Schottky Barrier, Fast Switching

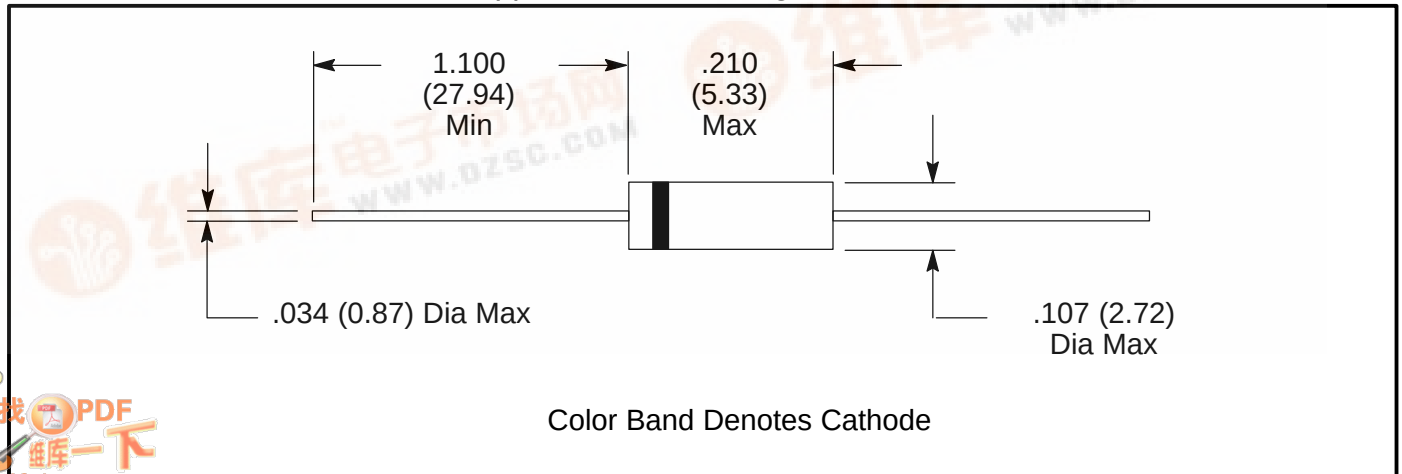
Features:

- Low Switching Noise
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Capability

Maximum Ratings and Electrical Characteristics: (T_A = +25°C unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Maximum Recurrent Peak Reverse Current 40V
Maximum RMS Voltage 28V
Maximum DC Blocking Voltage 40V
Maximum Average Forward Rectified Current (375” . (9.5mm) lead length at T_L = +95°C). . . 3.0A
Peak Forward Surge Current
(8.3ms single half sine–wave superimposed on rated load T_L = +75°C) 80A
Maximum Instantaneous Forward Voltage at 3A DC (Note 1) 525V
Maximum Average Reverse Current at Rated DC Blocking Voltage
T_A = +25°C 1.0mA
T_A = +100°C 10mA
Typical Thermal Resistance, Junction–to–Ambient (Note 2), R_{thJA} . . . . . 80°C/W
Typical Junction Capacitance (Note 3) 110pF
Operating Junction Temperature Range T_J . . . . . –65° to +125°C
Storage Temperature Range T_{STG} . . . . . –65° to +125°C

Note 1. measured at Pulse Width 300µs, Duty Cycle 2%.
Note 2. Thermal Resistance Junction to Ambient Vertical PC Board Mounting, 0.5” (12.7mm) Lead Length.
Note 3. Measured at 1MHz and applied reverse voltage of 4.0 Volts.



Color Band Denotes Cathode